

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S6	0	10/400469	USPAT	OR	ON	2004/12/13 13:28
S7	0	(memory adj cell) and (peripheral adj circuit) and (first adj conductive) and (secnod adj conductive) and gate and electrode and polysilicon and etch	USPAT	OR	ON	2004/12/13 13:30
S8	189	(memory adj cell) and (peripheral adj circuit) and (first adj conductive) and (second adj conductive) and gate and electrode and polysilicon and etch	USPAT	OR	ON	2004/12/13 13:31
S9	10	(memory adj cell) and (peripheral adj circuit adj transistor) and (first adj conductive) and (second adj conductive) and gate and electrode and polysilicon and etch	USPAT	OR	ON	2004/12/13 14:58
S10	1	("6340611").PN.	USPAT	OR	OFF	2004/12/13 14:59
S11	1	("6518642").PN.	USPAT	OR	OFF	2004/12/13 14:59
S12	1	("6818508").PN.	USPAT	OR	OFF	2004/12/13 14:59
S13	1	S10 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type)	USPAT	OR	ON	2004/12/13 15:04
S14	1	("6483749").PN.	USPAT	OR	OFF	2004/12/13 15:04
S15	1	S13 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type)	USPAT	OR	ON	2004/12/13 15:05

S16	1	S11 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type)	USPAT	OR	ON	2004/12/13 15:06
S17	1	S12 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type)	USPAT	OR	ON	2004/12/13 15:21
S18	1	S12 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type or high or voltage or withstand or constitutes or operate or power)	USPAT	OR	ON	2004/12/13 15:25
S19	1	S11 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type or high or voltage or withstand or constitutes or operate or power)	USPAT	OR	ON	2004/12/13 15:27

S20	1	S10 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type or high or voltage or withstand or constitutes or operate or power)	USPAT	OR	ON	2004/12/13 15:29
S21	1	("5296399"):PN.	USPAT	OR	OFF	2004/12/13 15:29
S22	1	S21 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type or high or voltage or withstand or constitutes or operate or power)	USPAT	OR	ON	2004/12/13 15:30
S23	1	("5852311"):PN.	USPAT	OR	OFF	2004/12/13 15:30
S24	1	S23 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type or high or voltage or withstand or constitutes or operate or power)	USPAT	OR	ON	2004/12/13 15:33
S25	1	("6555427"):PN.	USPAT	OR	OFF	2004/12/13 15:33

S26	1	S25 and (integrated or circuit or device or memory or cell or region or peripheric or peripheral or conductive or polysilicon or gate or electrode or serves or etch or etching or patterning or photo or transistor or charge or storage or floating or control or side or wall or spacer or oxide or nitride or silicon or insulation or isolation or substrate or n-type or p-type or high or voltage or withstand or constitutes or operate or power)	USPAT	OR	ON	2004/12/13 15:41
S27	2476	438/257	USPAT	OR	ON	2004/12/13 15:42
S28	1162	438/296	USPAT	OR	ON	2004/12/13 15:42
S29	548	438/267	USPAT	OR	ON	2004/12/13 15:42
S30	1045	438/270	USPAT	OR	ON	2004/12/13 15:42
S31	1085	438/299	USPAT	OR	ON	2004/12/13 15:43
S32	901	438/300	USPAT	OR	ON	2004/12/13 15:43
S33	535	438/594	USPAT	OR	ON	2004/12/13 15:43
S34	1270	438/595	USPAT	OR	ON	2004/12/13 15:43
S35	149	438/581	USPAT	OR	ON	2004/12/13 15:43
S36	181	438/583	USPAT	OR	ON	2004/12/13 15:43
S37	125	438/576	USPAT	OR	ON	2004/12/13 15:44
S38	830	438/649	USPAT	OR	ON	2004/12/13 15:44
S39	1278	438/655	USPAT	OR	ON	2004/12/13 15:44
S40	678	438/664	USPAT	OR	ON	2004/12/13 15:44
S41	1479	438/672	USPAT	OR	ON	2004/12/13 15:44
S42	225	438/673	USPAT	OR	ON	2004/12/13 15:44
S43	1156	438/680	USPAT	OR	ON	2004/12/13 15:45
S44	879	438/682	USPAT	OR	ON	2004/12/13 15:45
S45	1034	438/689	USPAT	OR	ON	2004/12/13 15:45
S46	1464	438/700	USPAT	OR	ON	2004/12/13 15:45
S47	283	438/721	USPAT	OR	ON	2004/12/13 15:45
S48	244	438/733	USPAT	OR	ON	2004/12/13 15:45
S49	541	438/740	USPAT	OR	ON	2004/12/13 15:45
S50	20	438/741	USPAT	OR	ON	2004/12/13 15:46
S51	342	438/742	USPAT	OR	ON	2004/12/13 15:46
S52	683	438/743	USPAT	OR	ON	2004/12/13 15:46
S53	393	438/744	USPAT	OR	ON	2004/12/13 15:46
S54	1480	438/745	USPAT	OR	ON	2004/12/13 15:46
S55	1782	438/706	USPAT	OR	ON	2004/12/13 15:46

S56	113	438/755	USPAT	OR	ON	2004/12/13 15:47
S57	672	438/756	USPAT	OR	ON	2004/12/13 15:47
S58	342	438/757	USPAT	OR	ON	2004/12/13 15:47

12/13/04